TO-252 P MOS

P-CHANNEL MOSFET in a TO-252 Plastic Package.

V_{DS}(V)=-100V I_D=-22A

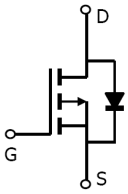
$R_{DS(ON)}$@-10V<70mΩ(Typ.67mR)

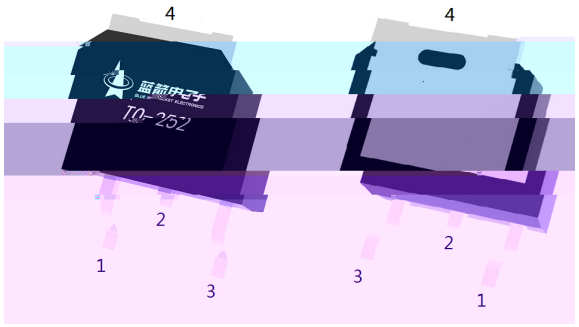
$R_{DS(ON)}$@-4.5V<85mΩ(Typ.70mR)

HF Product.

DC/DC

Power Management of Industrial DC/DC Converter.



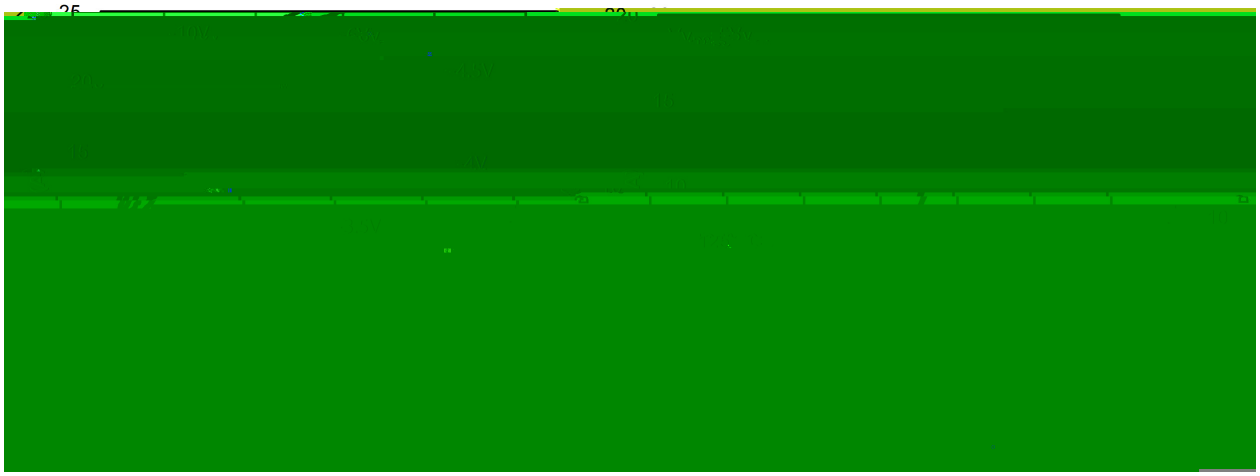


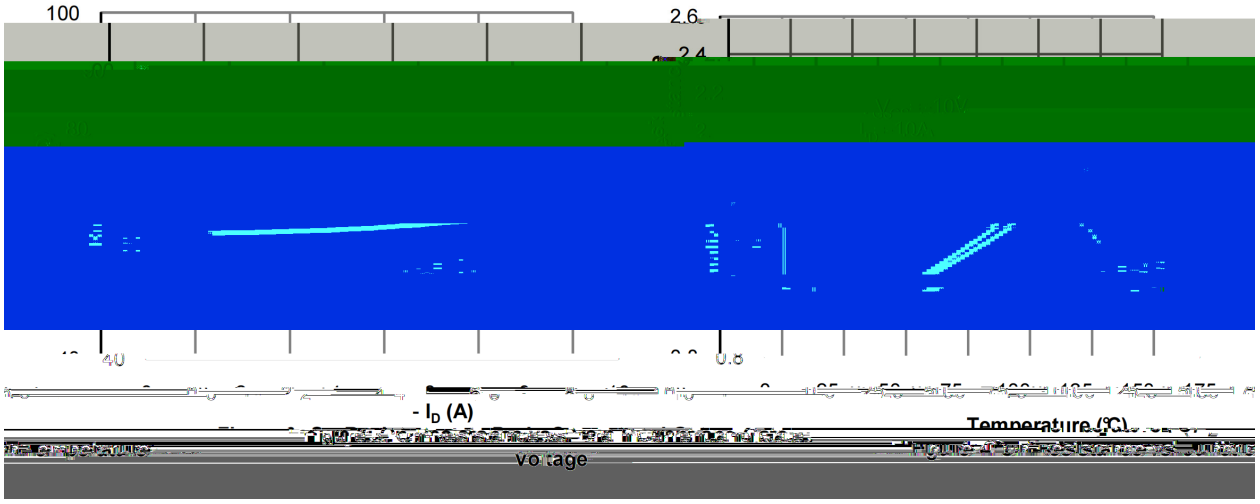
PIN1 G PIN 2 D PIN 3 S PIN 4 D

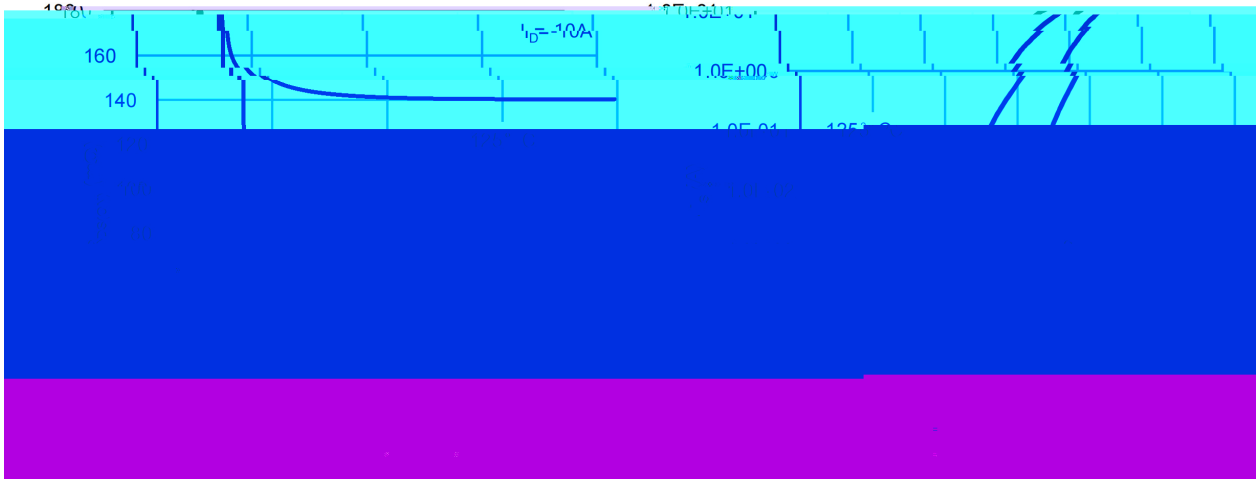
See Marking Instructions.

Parameter	Symbol	Rating	Unit
	V_{DS}	-100	V
Drain Current - Continuous	I_D(T_c=25)	-22	A
Drain Current – Pulsed	I_{DM}	-66	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D(T_c=25)	75	W
Single Pulse Avalanche Energy(L=0.5mH)	E_{AS}	176.4 6	mJ
Avalanche Current(Note)			

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=-10V V_{DS}=-50V R_L=10Ω R_{GEN}=3Ω		6		ns
Turn-On Rise Time	t_r			2.4		
Turn-Off Delay Time	$t_{d(off)}$			19		
Turn-Off Fall Time	t_f			2.6		




100
2.6
2.4
40
0.8
- I_D (A)
Temperature (℃)
voltage


160
140
I_D=-10A
1.0E+00

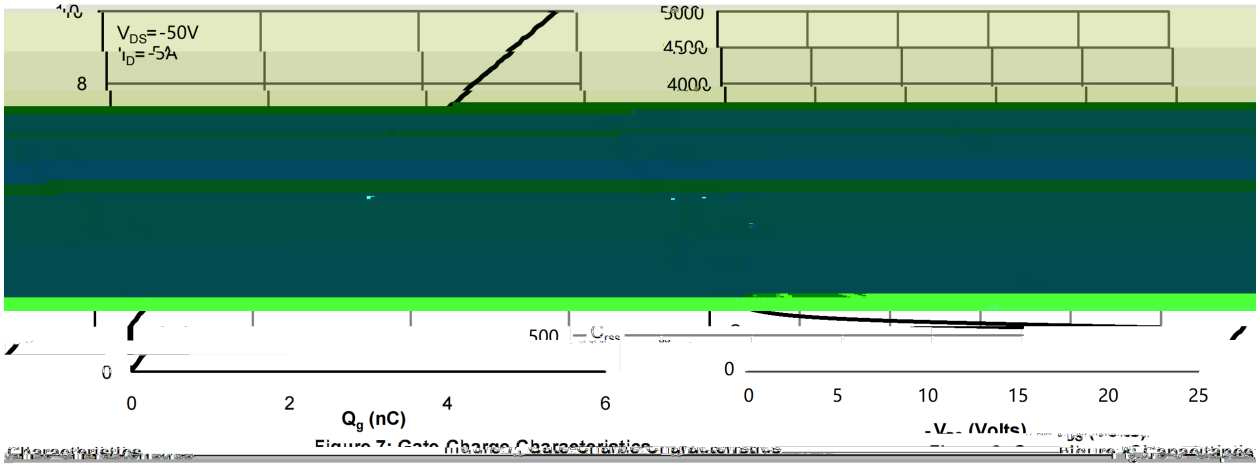
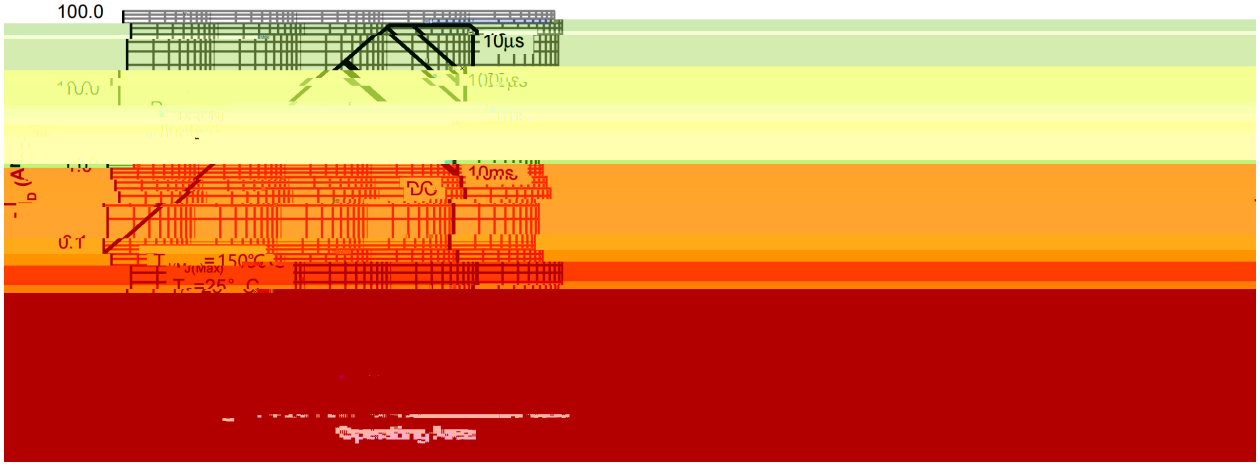
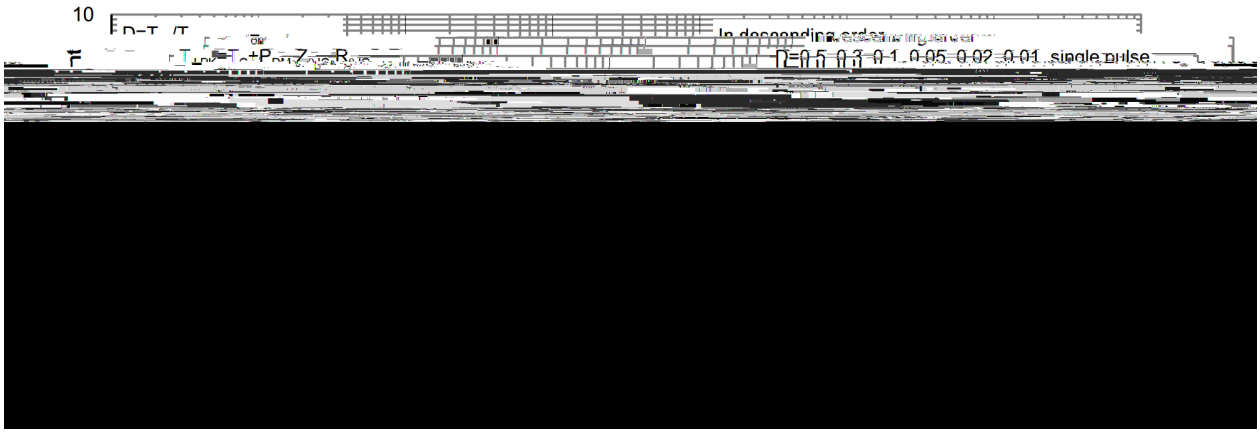
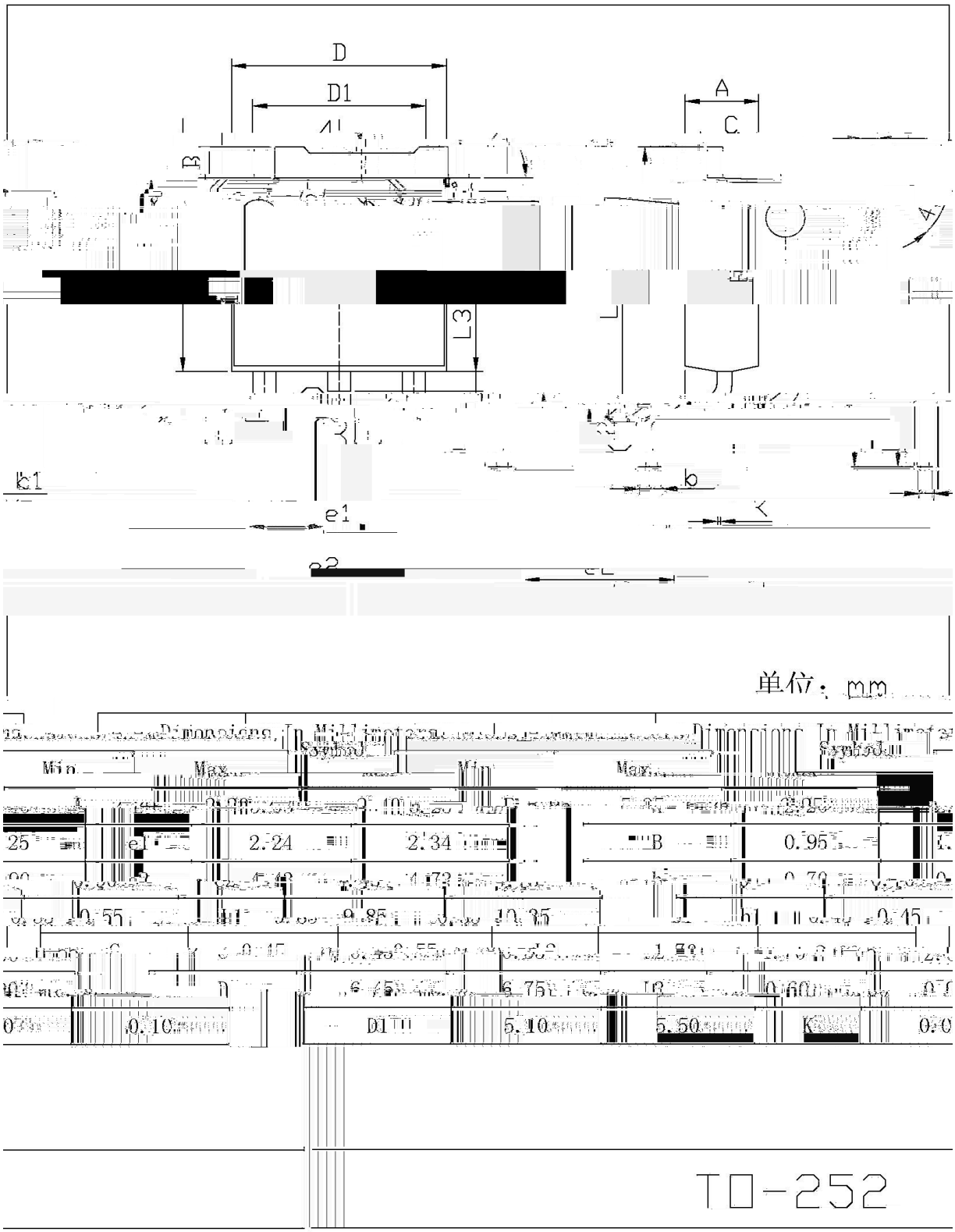
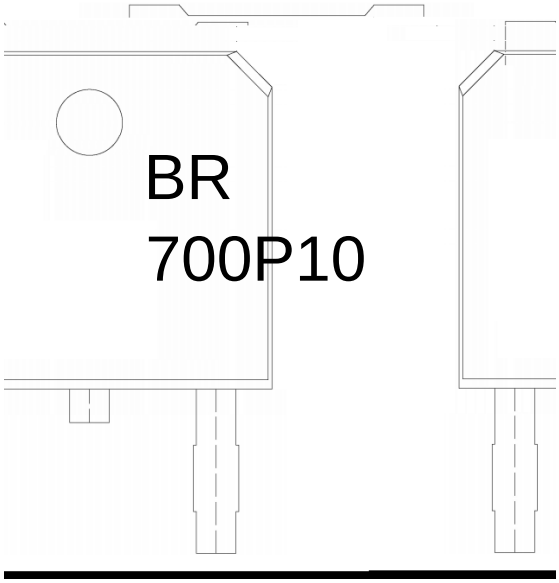


Figure 7: Gate Charge Characteristics






D
D1
A
C
B
L3
k1
e1
b
K
e2
单位：mm
Dimensions In Millimeters
Symbol
Min
Max
2.24
2.34
B
0.95
0.55
0.85
0.10
D1
5.10
5.50
TO-252



BR

700P10

****

Note:

BR:	Company Code
700P10:	Product Type
****:	Lot No. Code, code change with Lot No